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FDS9945

60V N-Channel PowerTrench MOSFET

General Description

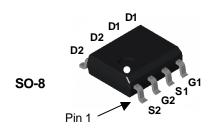
These N Channel Logic Level MOSFET have been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

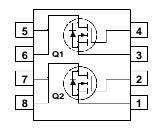
The MOSFET feature faster switching and lower gate charge than other MOSFET with comparable RDS(on) specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 3.5 A, 60 V. $R_{DS(ON)} = 0.100\Omega$ @ $V_{GS} = 10$ V $R_{DS(ON)} = 0.200\Omega$ @ $V_{GS} = 4.5$ V
- Optimized for use in switching DC/DC converters with PWM controllers
- · Very fast switching
- Low gate charge.





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	V
Ь	Drain Current - Continuous	(Note 1a)	3.5	A
	- Pulsed		10	
P _D	Power Dissipation for Single Operation	(Note 1a)	2	W
		(Note 1b)	1.6	
		(Note 1c)	1.0	
T _J , T _{STG}	Operating and Storage Junction Temperat	ture Range	-55 to +175	°C

Thermal Characteristics

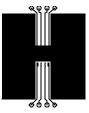
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78 (steady state), 50 (10 sec)	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1c)	135	°C/W
R ₀ JC	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
FDS9945	FDS9945	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			I	I	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to $25^{\circ}C$		62.5		mV/°C
l _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)			•		
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1	2.5	3	V
ΔV _{GS(th)} ΔT _J	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-6		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, \qquad I_D = 3.5 \text{ A}$ $V_{GS} = 4.5 \text{V}, \qquad I_D = 2.5 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 3.5 \text{A}, T_J = 125 ^{\circ}\text{C}$		74 103 126	100 200 170	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, = V_{DS} = 30 \text{ V}$	10			Α
g fs	Forward Transconductance	$V_{DS} = 5V$, $I_D = 3.5 A$		8.6		S
Dvnamic	Characteristics			ı		
Ciss	Input Capacitance	$V_{DS} = 30 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		420		pF
Coss	Output Capacitance	f = 1.0 MHz		48		pF
C _{rss}	Reverse Transfer Capacitance			20		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, \qquad I_{D} = 1 \text{ A},$		7	14	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		4.3	8.6	ns
t _{d(off)}	Turn-Off Delay Time			19	34	ns
t _f	Turn-Off Fall Time			3	6	ns
Q_g	Total Gate Charge	$V_{DS} = 30 \text{ V}, \qquad I_{D} = 3.5 \text{ A},$		8	13	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$		4		nC
$\overline{Q_{gd}}$	Gate-Drain Charge	1		2.5		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings	•	•	•	
ls	Maximum Continuous Drain–Source	<u> </u>			2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.1 A (Note 2)		0.8	1.2	V

^{1.} R_{NA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°/W when mounted on a 0.5in² pad of 2 oz copper



b) 125°/W when mounted on a 0.02 in² pad of 2 oz copper



c) 135°/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width $< 300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

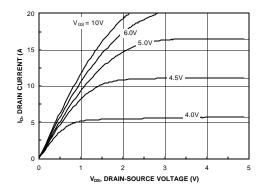


Figure 1. On-Region Characteristics.

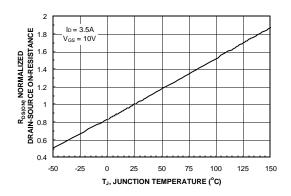


Figure 3. On-Resistance Variation with Temperature.

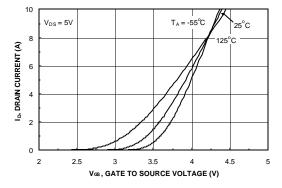


Figure 5. Transfer Characteristics.

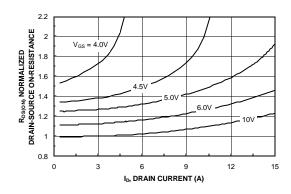


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

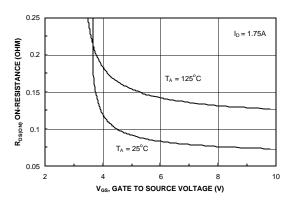


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

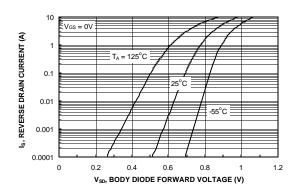
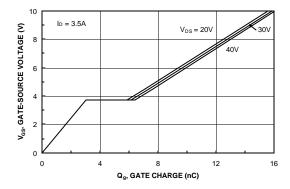


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



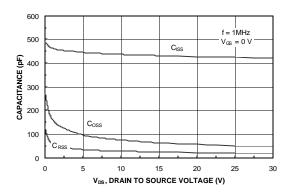
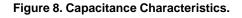
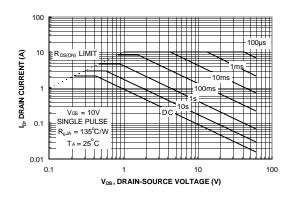


Figure 7. Gate Charge Characteristics.





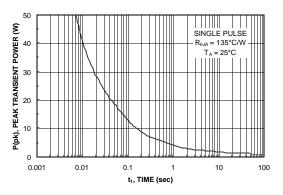


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

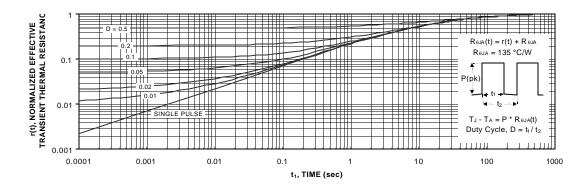


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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